ESM1600B

QUAD COMPARATOR INTERFACE CIRCUIT

MINIMUM HYSTERESIS VOLTAGE AT EACH INPUT : 0.3 V

SGS-THOMSON MICROELECTRONICS

- OUTPUT CURRENT : 15 mA
- LARGE SUPPLY VOLTAGE RANGE : + 10 V to + 35 V
- INTERNAL THERMAL PROTECTION
- INPUT AND OUTPUT CLAMPING PROTEC-TION DIODES.

DESCRIPTION

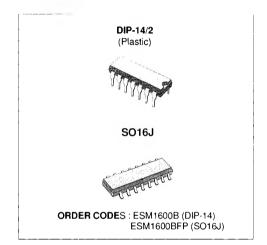
The ESM1600B is a quadruple comparator intented to provide an interface between signal processing and transmitting lines in very noisy industrial surroundings.

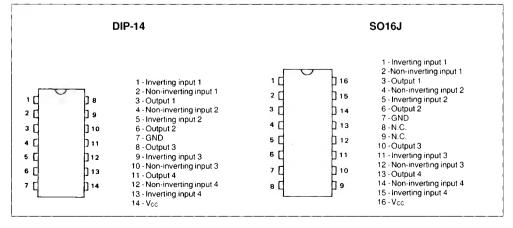
Output of each comparator, used as line driver, supplies a constant current (PNP output stage) and is specially well protected against powerful overvoltages. The open collector output circuit allows the connection of several comparators to a single transmitting line.

The ESM1600B can operate as receiver on a line transmitting noisy high-voltage signals. Hysteresis effect, internally implemented on inputs of each comparator provides an excellent noise immunity. In addition, each input is also protected against overvoltages.

The ESM1600B can operate in a wide supply voltage range (standard operational amplifier \pm 15 V supply or single + 12 V or + 24 V supplies used in industrial electronic sets).

Moreover, internal thermal protection circuitry cuts out the output current of the four comparators when power dissipation becomes excessive.





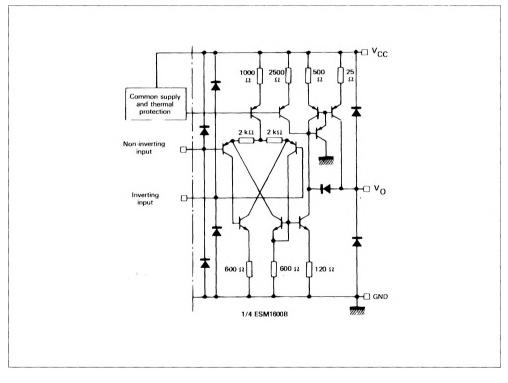
PIN CONNECTIONS (top view)

September 1988

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{cc}	Supply Voltage	45	V	
VID	Differential Input Voltage	45	V	
V ₁	Input Voltage	- 0.7 to + 45	v	
I _{O (max)}	Output Current	Internally Limited	mA	
Ptot	Power Dissipation	Internally Limited	w	
Top	Operating Ambient Temperature Range	- 25 to + 85	°C	
Tstg	Storage Temperature Range	- 40 to + 150	°C	

SCHEMATIC DIAGRAM





ELECTRICAL CHARACTERISTICS V_{CC} = + 35 V, - 25 °C $\leq T_{amb} \leq$ + 85 °C (unless otherwise specified)

Symbol	Parameter	Value				
		Min.	Тур.	Max.	Unit	Fig.
V_1^*	Input Voltage Range - Note 1				v	
Vī	Non-inverting Input Inverting Input	0 2	_	33 33		
V _C	Input Control Voltage (2 V < V _{CM} < 33 V) - Note 2	150	-	500	mV	1
I _{IB}	Input Bias Current - Note 3	-	1	5	μA	-
Isc	Short-circuit Output Current V_{CC} = + 10 to + 35 V	6	-	25	mA	2
$V_{CC}-V_{O}$	Output Saturation Voltage (high level) - ($I_{O} = -10$ mA)	-	1	1.5	V	3
I _{OL} I _{OH}	Output Off-state Current (V ₁ ⁺ = 2 V, V ₁ ⁻ = 33 V)	-	1	5	μΑ	4
Icc	Supply Current					
	$R_L = \infty$ for the 4 Comparators R_L Common for the 4 Comparators	_	3 9	5 12	mA	5
Svo	Output Slew-rate ($R_L = 3 \text{ k}\Omega$, $T_{amb} = +25 \text{ °C}$)	1	-	-	V/µs	-
VF	Input Protective Diode Forward Voltage (I = 20 mA, T_{amb} = + 25 °C)	-	-	1.5	V	-
-	Energy of Pulses against which Circuit Output is Protected. $(T_{amb} = + 25 \text{ °C})$ - Note 4	-	÷	20	mJ	-
-	Pulsed Current Applied to Protective Output Diodes $(T_{amb} = + 25 \text{ °C}) \cdot \text{Note 5}$	-	0.4	_	A	6

Notes: 1. When negative input is biased between 0 and 2 volts output is always low.

 Comparator hysteresis voltage on positive input on the one hand and negative input on the other hand equals sum of input control voltages V_{C1} + V_{C2} or V_{C3} + V_{C4}.

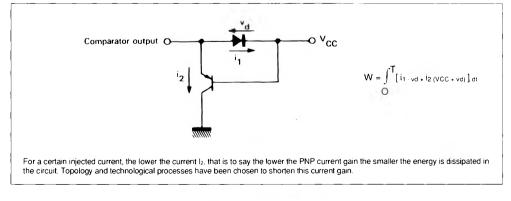
Input current flows out of the circuit owing to PNP input stage. This current is constant and independent of output level. So no load change is transmitted to inputs.

4. By definition, a circuit is immunized against powerful signals when no durable characteristic change occurs after the application of these signals and when the circuit has not been destroyed.

In industrial surroundings, parasitic signals contain usually high voltage (over 200 V) AC harmonics having variable impedance of 500 Ω to 10 K Ω .

The power dissipation of these signals is divided between clamping diodes and the V_{cc}. Simulation is used to determine the maximum energy level. The injected current value cannot in any case exceed 3 A.

5. Output protective diodes are tested individually by means of positive and negative discharge voltages of a capacitor. The negative discharge control occurs through a single diode. During positive discharge, due to the properties of integration, a grounded collector PNP transistor appears in parallel with the clamping diode connected to V_{CC}. A part of the current flows through this transistor, V_{CE} being greater than V_{CC}. If T is the total discharge duration, energy dissipated in the circuit is:





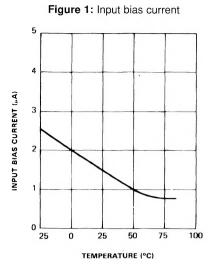


Figure 3: Output saturation voltage

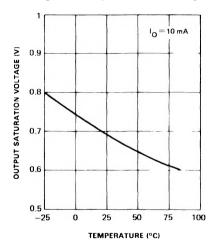


Figure 2: Output saturation voltage

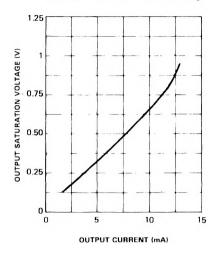
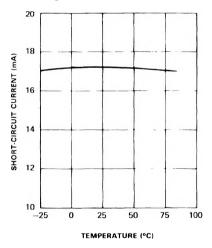


Figure 4: Short circuit corrent





TYPICAL APPLICATIONS

Figure 5 : Conversion of DTL, TTL, MOS Signals on a Transmitting Line.

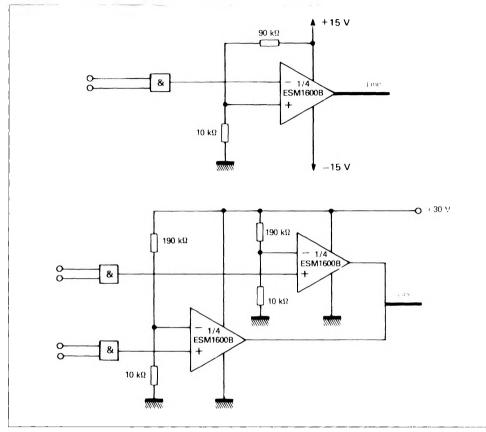
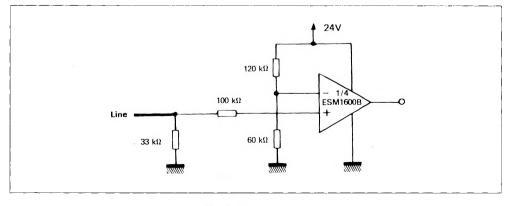


Figure 6 : Reception of Highly Noisy Signals.





ESM1600B

TEST CIRCUIT

Figure 7.

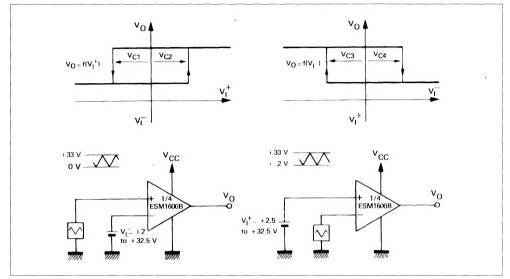
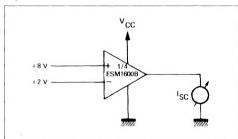


Figure 8.

Figure 9.



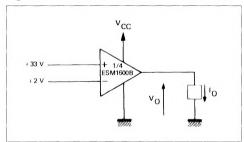
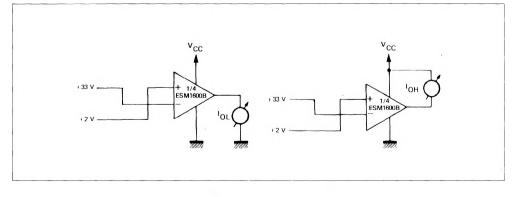


Figure 10.





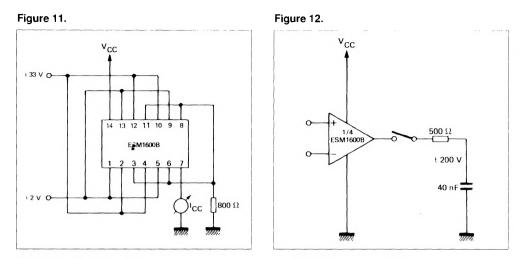


Figure 13 : Response Time.

